

<b>INFORMATION DISCLOSURE CITATION</b> (Use several sheets if necessary)	Docket Number	11188.00	Application Number
	Applicant(s)		
	Kyung Joon Han et al.		
#2	Filing Date	November 8, 2001	Group Art Unit
			2818

J1017 U.S. PTO  
 10/039518  
 11/08/01

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
HND	A	5,060,195	10/22/91	Gill et al.			
	B	5,418,741	05/23/95	Gill			
	C	5,487,033	01/23/96	Keeney et al.			
	D	5,546,340	08/13/96	Hu et al.			
	E	5,553,020	09/03/96	Keeney et al.			
	F	5,646,886	07/08/97	Brahmbhatt			
	G	5,659,504	08/19/97	Bude et al.			
	H	5,959,892	09/28/99	Lin et al.			
HND	I	6,175,519	01/16/01	Lu et al.			

**FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

HND	J	J. D. Bude et al.; <u>Monte Carlo Simulation of the CHISEL Flash Memory Cell</u> ; IEEE Transactions on Electron Devices, Vol. 47, No. 10, October 2000; p. 1873-1881
HND	K	J.D. Bude et al.; <u>EEPROM/Flash Sub 5.0V Drain-Source Bias Hot Carrier Writing</u> , IEDM Technical Digest, 1995, p. 989-991
HND	L	J.D. Bude et al.; <u>Secondary Electron Flash – a High Performance, Low Power Flash Technology for 0.35 μm and Below</u> ; IEDM Technical Digest, 1997, p. 279-282

EXAMINER	H. Ho	DATE CONSIDERED	March 4, 2003
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609, Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.